



LIFETIME FACTORS IN SILICON



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AMERICAN SOCIETY FOR
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LIFETIME FACTORS IN SILICON

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15-16 Feb. 1979

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R. D. Westbrook, Oak Ridge National
Laboratory, symposium chairman

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Foreword

The symposium on Lifetime Factors in Silicon was held in San Diego, Calif., on 15-16 Feb. 1979. The American Society for Testing and Materials, through its Committee F-1 on Electronics, sponsored the event, and R. D. Westbrook, Oak Ridge National Laboratory, presided as chairman. The section chairmen were P. H. Langer, Bell Telephone Laboratories, F. G. Vieweg-Gutberlet, Wacker-Chemitronic, and C. W. Pearce, Western Electric Company.

The symposium committee, to whom appreciation is extended, was composed of the following members:

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R. D. Westbrook

Symposium chairman and chairman of the
symposium committee.

Related ASTM Publications

**1980 Annual Book of ASTM Standards, Part 43, Electronics, \$49.00,
01-043080-46**

Spreading Resistance, STP 572 (1975), \$3.55, 04-572000-46

A Note of Appreciation to Reviewers

This publication is made possible by the authors and, also, the unheralded efforts of the reviewers. This body of technical experts whose dedication, sacrifice of time and effort, and collective wisdom in reviewing the papers must be acknowledged. The quality level of ASTM publications is a direct function of their respected opinions. On behalf of ASTM we acknowledge with appreciation their contribution.

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